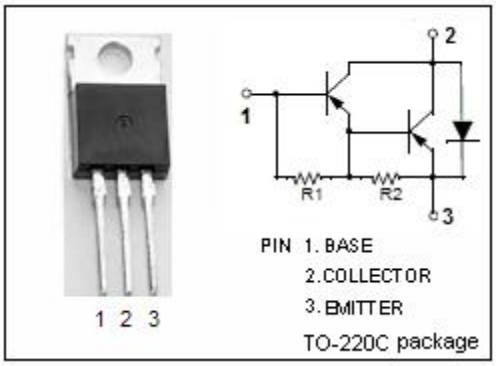
isc Silicon PNP Darlington Power Transistor 2SB1087

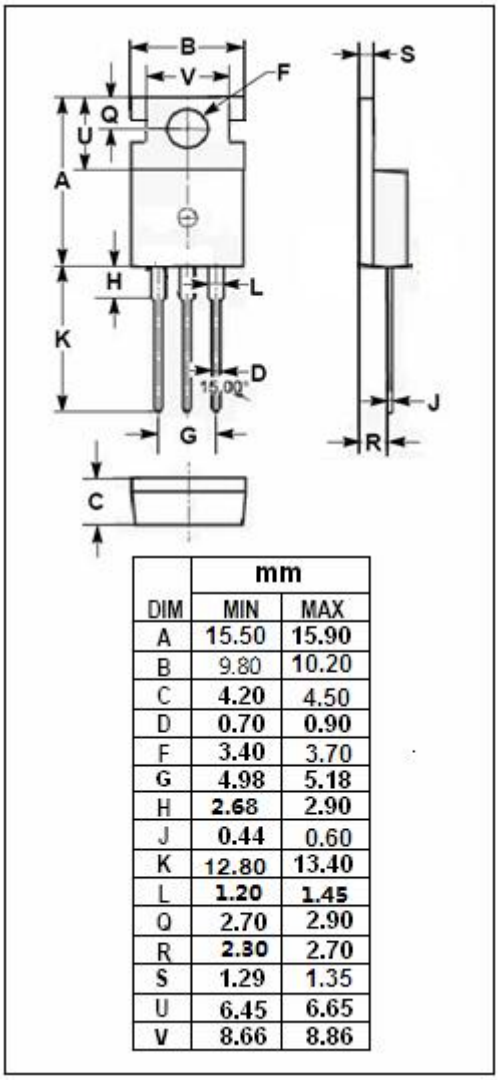
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -100V(Min)
- High DC Current Gain-
  : h_{FE}= 2000(Min)@ (V_{CE}= -2V, I_C= -2A)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for low frequency power amplifiers and low speed switching applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-10	A
I_B	Base Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @T_a=25℃	2	W
	Collector Power Dissipation @T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -2mA			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -2mA			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V ; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-3	mA
h_{FE-1}	DC Current Gain	I_C= -2A; V_{CE}= -2V	2000		20000	
h_{FE-2}	DC Current Gain	I_C= -4A; V_{CE}= -2V	500			

◆ **h_{FE-1} Classifications**

M	L	K
2000-5000	4000-10000	8000-20000